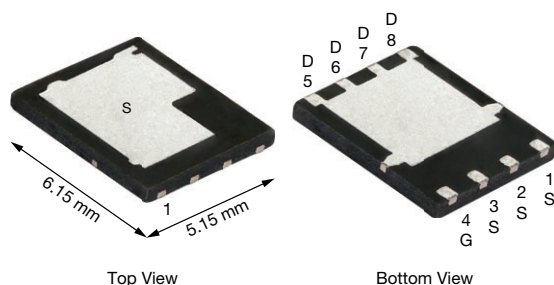


N-Channel 30 V (D-S) MOSFET

PowerPAK® SO-8DC



Top View

Bottom View

PRODUCT SUMMARY

V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.00062
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.00093
Q_g typ. (nC)	59.7
I_D (A)	100 ^{a, g}
Configuration	Single

FEATURES

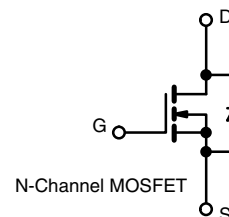
- TrenchFET® Gen IV power MOSFET
- Top side cooling feature provides additional venue for thermal transfer
- Optimized Q_g , Q_{gd} , and Q_{gd}/Q_{gs} ratio reduces switching related power loss
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- Synchronous buck converter
- OR-ing
- Load switching
- Battery management



N-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK SO-8DC
Lead (Pb)-free and halogen-free	SiDR392DP-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	+20 / -16	V
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	100 ^a	A
	$T_C = 70$ °C	100 ^a	
	$T_A = 25$ °C	82 ^{b, c}	
	$T_A = 70$ °C	66 ^{b, c}	
Pulsed drain current ($t = 100$ μ s)	I_{DM}	200	A
Continuous source-drain diode current	$T_C = 25$ °C	100	A
	$T_A = 25$ °C	5.6 ^{b, c}	
Single pulse avalanche current	I_{AS}	45	mJ
Single pulse avalanche energy	E_{AS}	101	
Maximum power dissipation	$T_C = 25$ °C	125	W
	$T_C = 70$ °C	80	
	$T_A = 25$ °C	6.25 ^{b, c}	
	$T_A = 70$ °C	4 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^c		260	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	R_{thJA}	15	20	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.8	1	
Maximum junction-to-case (source)	R_{thJC}	1.1	1.4	

Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8DC is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 54 °C/W
- $T_C = 25$ °C



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = 10 mA	-	15	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	-	-5.3	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	-	2.2	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 / -16 V	-	-	100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15	
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	20	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.00047	0.00062	Ω
		V _{GS} = 4.5 V, I _D = 15 A	-	0.00071	0.00093	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	-	125	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	-	9530	-	pF
Output capacitance	C _{oss}		-	4280	-	
Reverse transfer capacitance	C _{rss}		-	626	-	
Total gate charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A	-	125	188	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A	-	59.7	90	
Gate-source charge	Q _{gs}		-	25.2	-	
Gate-drain charge	Q _{gd}		-	12.3	-	
Gate resistance	R _g	f = 1 MHz	0.1	0.4	0.8	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω, I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	17	35	ns
Rise time	t _r		-	23	50	
Turn-off delay time	t _{d(off)}		-	41	80	
Fall time	t _f		-	12	25	
Turn-on delay time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω, I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	-	40	80	
Rise time	t _r		-	66	135	
Turn-off delay time	t _{d(off)}		-	50	100	
Fall time	t _f		-	35	70	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	100	A
Pulse diode forward current	I _{SM}		-	-	200	
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.7	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	-	80	160	ns
Body diode reverse recovery charge	Q _{rr}		-	144	290	nC
Reverse recovery fall time	t _a		-	43	-	ns
Reverse recovery rise time	t _b		-	37	-	

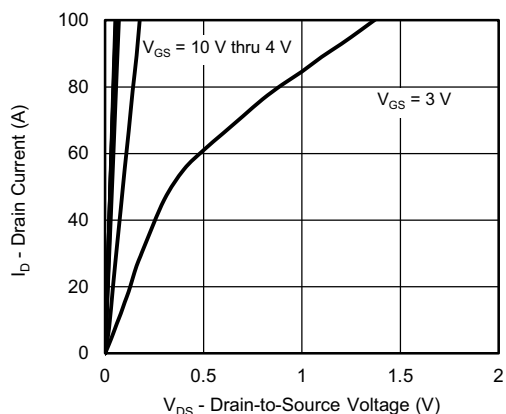
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

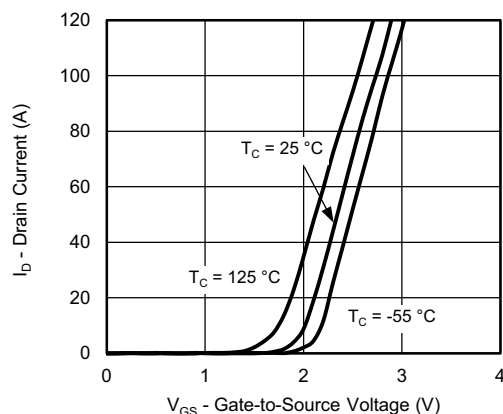
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



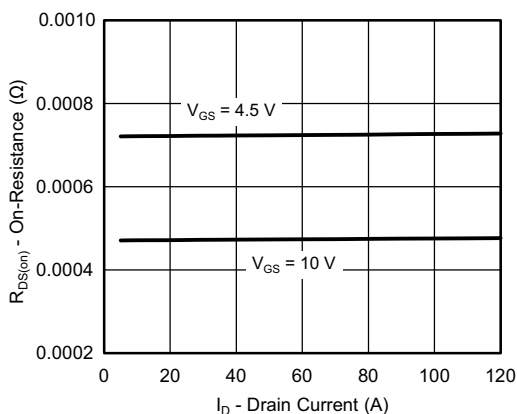
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



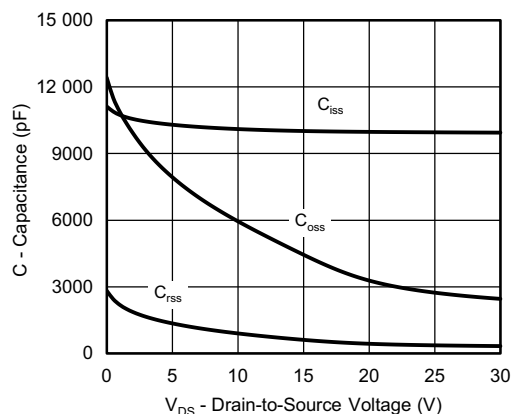
Output Characteristics



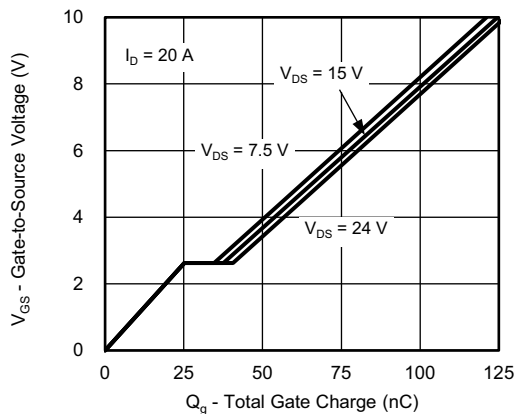
Transfer Characteristics



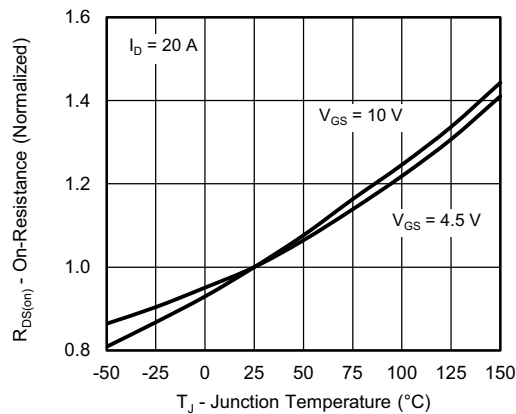
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



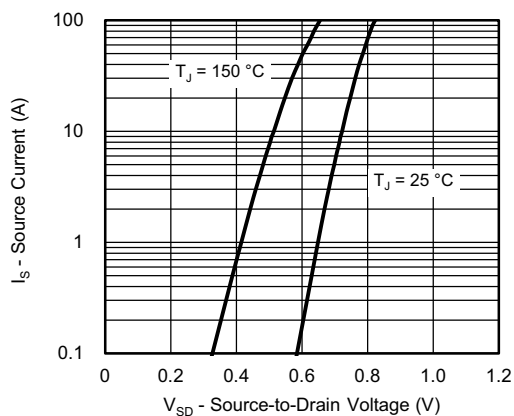
Gate Charge



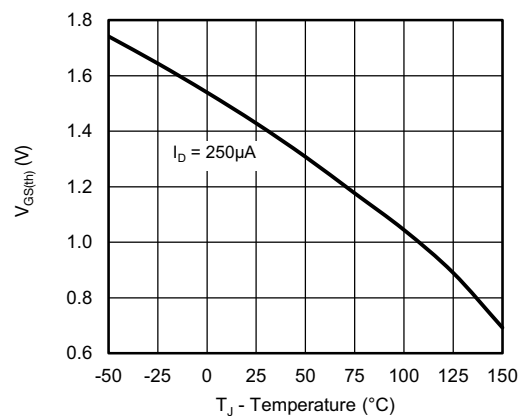
On-Resistance vs. Junction Temperature



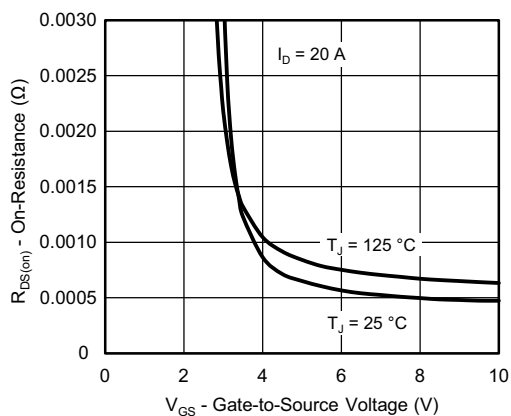
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



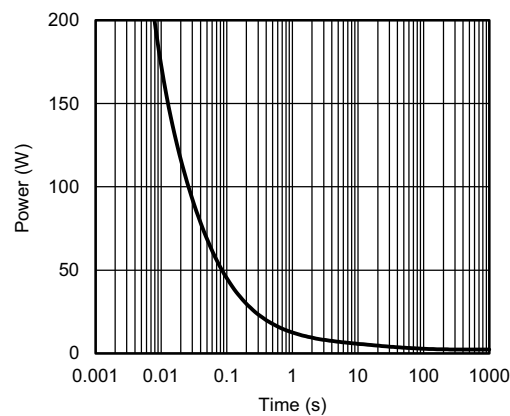
Source-Drain Diode Forward Voltage



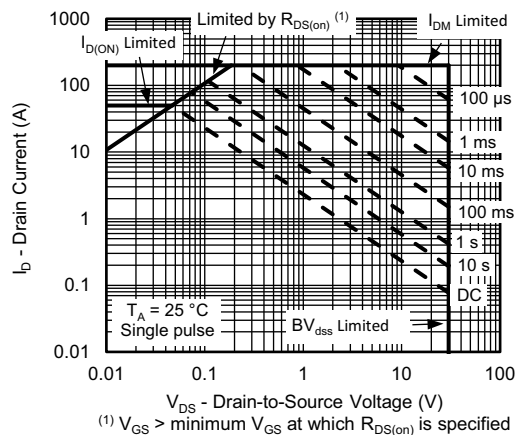
Threshold Voltage



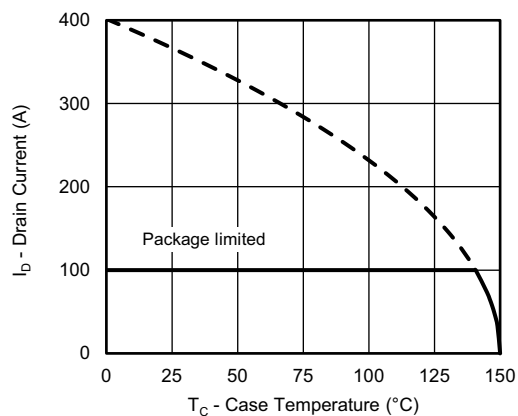
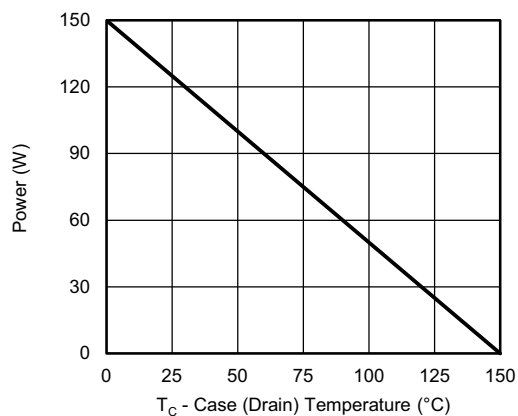
On-Resistance vs. Gate-to-Source Voltage



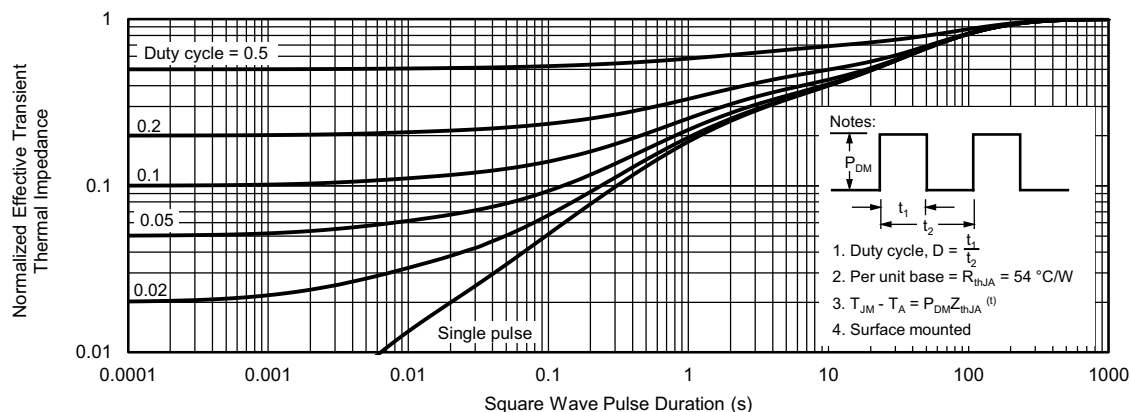
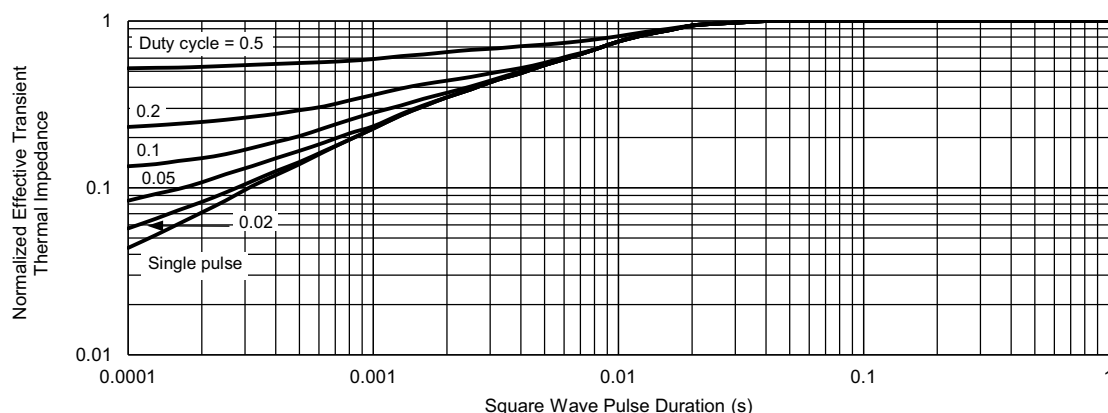
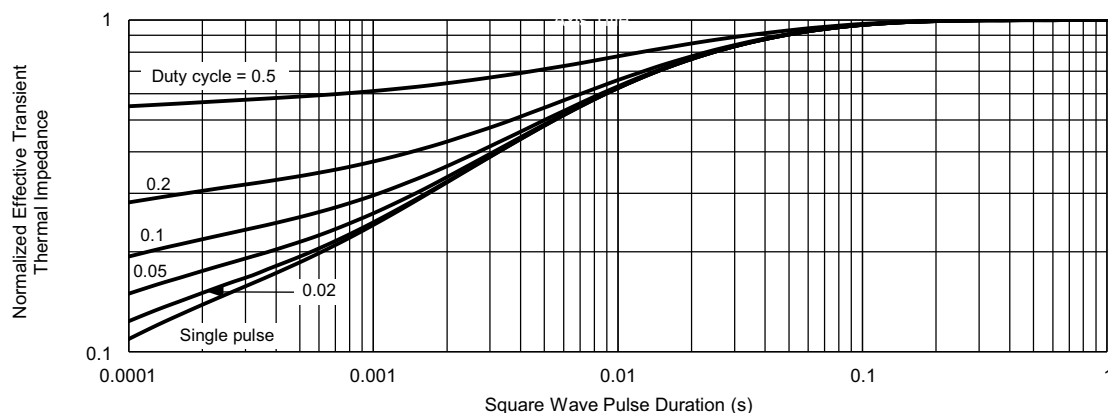
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Case
Note

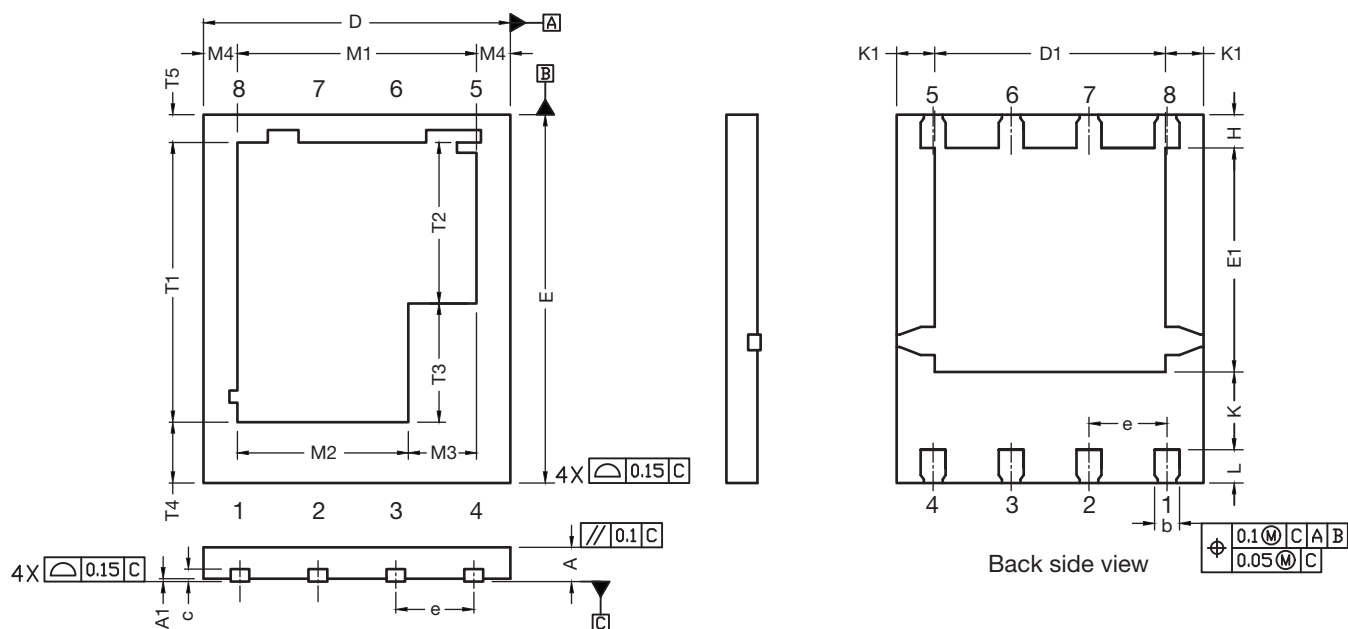
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case (Drain)

Normalized Thermal Transient Impedance, Junction-to-Case (Source)

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PowerPAK® SO-8 Double Cooling Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.51	0.56	0.61	0.012	0.014	0.016
A1	0.00	0.02	0.05	0.000	0.0008	0.002
b	0.36	0.41	0.46	0.014	0.016	0.018
c	0.15	0.20	0.25	0.006	0.008	0.010
D	4.90	5.00	5.10	0.193	0.197	0.201
D1	3.71	3.76	3.81	0.146	0.148	0.150
e	1.27 BSC			0.050 BSC		
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	3.60	3.65	3.70	0.142	0.144	0.146
H	0.49	0.54	0.59	0.019	0.021	0.023
K	1.22	1.27	1.32	0.048	0.050	0.052
K1	0.64 typ.			0.025 typ.		
L	0.49	0.54	0.59	0.019	0.021	0.023
M1	3.85	3.90	3.95	0.152	0.154	0.156
M2	2.74	2.79	2.84	0.108	0.110	0.112
M3	1.06	1.11	1.16	0.042	0.044	0.046
M4	0.56 typ.			0.022 typ.		
N	8			8		
T1	4.51	4.56	4.61	0.178	0.180	0.182
T2	2.58	2.63	2.68	0.102	0.104	0.106
T3	1.88	1.93	1.98	0.074	0.076	0.078
T4	0.97 typ.			0.038 typ.		
T5	0.48 typ.			0.019 typ.		
ECN: T16-0445-Rev. A, 11-Jul-16						
DWG: 6048						

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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